AN9D, AN9E, AN9F Series

Analog master slice IC series

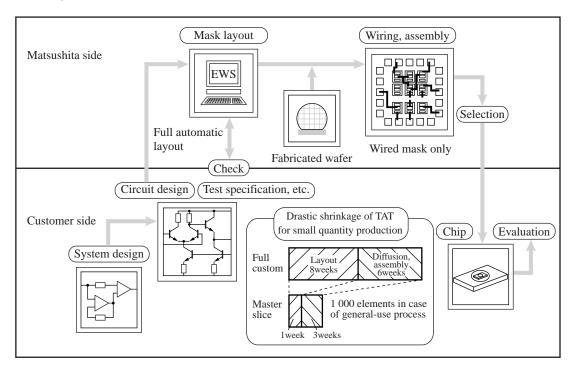
Overview

The AN9D, AN9E and AN9F series are master slice ICs of bipolar process, which enables you to integrate an analog circuit easily onto a single chip. A custom IC can be made by placing a wired pattern designed in line with the customer's analog circuit onto a master slice.

Starting from a wafer on which a most part of IC diffusion processes are already finished, you can shorten an IC pilot fabrication considerably. Further, placement of elements and inter-element wiring are done automatically by a computer, which results in short period of pattern designing and thereby developing a custom IC in a short period.

Features

- High design flexibility
 - Easy circuit constant design because of setting resistance or capacitance to an arbitrary value.
 - Free setting of contacts between a substrate and GND wiring prevents from operation error to be caused by floating of substrate potential.
 - Usable for multi power source because a resistor island potential can be set for each unit.
 - Builds in a lateral type PNP transistor of high reverse breakdown voltage between base and emitter, or a collector wall type NPN transistor of excellent saturation characteristics. (AN9DA00, AN9DB00, AN9DF00)
- Short development period
 - Due to a full automatic layout design, a sample is available in one month from a completion of a circuit diagram.
- Applicable to a small quantity production item
 - Possible to develop a custom IC for small quantity production due to a low development cost.

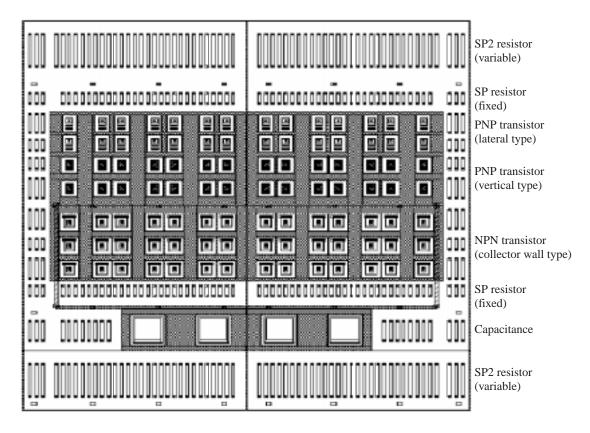


Development Flow

Product Mix

Series name	Supply voltage		Elerr					
		NPN transistor			PI	VP transis	Remarks	
		f _{T(max)}	BV_{CEO}	h _{FE}	f _{T(max)}	BV_{CEO}	h _{FE}	
AN9D series	to 12 V	2.6 GHz	14.4 V	100 to 250	1.0 GHz	14.4 V	66 to 200	For low power dissipation/ high speed operation IC
AN9E series	to 12 V	3.5 GHz	14.4 V	80 to 250	1.5 GHz	14.4 V	50 to 130	For Bi-CMOS IC
AN9F series	to 30 V	300 MHz	30 V	80 to 250	9 MHz	30 V	80 to 350	For high breakdown voltage IC

■ Basic Block Configuration (AN9DA00, AN9DB00, AN9DF00)



- AN9D series (V_{CC} = to 12 V, $f_{T(max)}$ = 2.6 GHz)
 - High speed low power dissipation process
 - Constant-variable resistor and capacitor elements built in
 - Large current transistor built in (AN9DA00, AN9DB00, AN9DF00)
 - Optimal for a control-system application due to built-in collector wall type NPN transistors and lateral PNP transistors (AN9DA00, AN9DB00, AN9DF00)
 - Optimal for signal processing application due to built-in high speed NPN transistors and vertical PNP transistors (AN9DC00, AN9DD00, AN9DE00)
 - IIL element built-in (AN9DF00)

Product name		AN9DA00	AN9DB00	AN9DC00	AN9DE00	AN9DD00*	AN9DF00	Remarks	
Pad count		28	36	55	64	75	32		
Total e	Total element count		1 287	2 424	3 854	5 106	6 602	1 607	
Transis	Transistor count		306	600	920	1 288	1 610	306	
		A11			320	448	560		Basic size
	NIDNI	A21			160	224	280		Double size
	NPN	A62P	8	8				8	62 times size
		B11	126	252				126	Basic size (CW winding)
		LA1	84	168				84	Basic size (Lateral type)
		LA4S	4	4				4	8 times size (Lateral type)
	PNP	V11	84	168	320	448	560	84	Basic size (Vertical type)
		V21			120	168	210		Double size (Vertical type)
Gate co	ountIIL				320				
Resisto	or count		969	1 800	2 854	3 706	4 852	969	
	SP	$5 \ k\Omega$	474	888	1 408	1 728	2 440	474	
		10 kΩ	198	336	480	640	800	198	
	SP2	2.5 kΩ	297	576	966	1 338	1 612	297	Resistance variable
Capacit	tor count	5 pF	12	24	80	112	140	12	

Note) *: Under development

- AN9E series (V_{CC} = to 12 V, $f_{T(max)} = 3.5$ GHz)
 - Bi-CMOS process adopted
 - Constant-variable resistor and capacitor elements built in
 - Gate array and standard cell built in
 - Zener zap elements built in

Pro	Product name			AN9EB00*	Remarks		
Pad cou	ınt		40	55			
Total element count			8 830	14 033			
Transis	tor cour	nt	900	1 402			
[N21	420	588	Double size		
	NPN	N54	20	34	40 times size		
		A42G	20	96			
	DND	P21	420	588	Double size (Vertical type)		
	PNP	V42G	20	96			
Resistor	r count		5 016	7 138			
		$40 \ k\Omega$	90	160			
	SP	$10 \ k\Omega$	1 440	2 016			
		5 kΩ	1 680	2 352			
	DC	$5 \mathrm{k}\Omega$	1 086	1 602	Resistance variable		
	PS	$2 \ k\Omega$	720	1 008	Resistance variable		
Capacito	Capacitor count 5 pF		60	84			
Diode c	ount		30	42			
	Z	D1	30	42	Zener zap element		
MOS co	ount		12	32			
	N-1	MOS	6	16	60/2		
	P-I	MOS	6	16	30/2		
Gate ar	ray cou	nt	2 800	5 400			
	LC	OGIC	2 800	5 400	Use rate 35% or less		
Standard cell count		12	19				
[Analog SW		6	12			
Ī	Anal	og SW	4	4			
	8-bi	t DAC	1	1			
	Oscillat	ion circuit	1	2			

Note) *: Under development

- AN9F series (V_{CC} = to 30 V, $f_{T(max)} = 300 \text{ MHz}$)
 - High voltage process adopted
 - Constant-variable resistor and capacitor elements built in
 - Built-in Zener diode for simplified reference voltage
 - Output-circuit-exclusive three blocks are built in
 - ZAP-adopted reference-voltage-exclusive one block is built in

Product name				AN9FA00	Remarks		
Pad count					36		
Total element count					1 655		
Transistor	Transistor count				308		
			N11X	72	Basic size		
		NPN	W11X	72	Basic size (surrounded with DN)		
			N100X	8	100 times size		
		DND	YA1	144	Basic size (Lateral type)		
	PNP YX1DP			12	Emitter and collector are surrounded with DN		
Resistor co	Resistor count		1 308				
			2 kΩ	1 068	Resistance variable		
		SP	5 kΩ	48	Resistance variable		
		DW	10 kΩ	136			
		PW	50 kΩ	56			
Capacitor count 7.5		7.5 pF	24	Capacitance variable			
Diode count ZD ZB2		ZB2	15	Bulk Zener diode			
Special block Output circuit		circuit	3	250 times size transistor built-in			
Reference power supply circuit			oly circuit	1	2.5 V reference power supply circuit		

■ Circuit Library

General-use basic circuits are available as libraries.

Circuit name	Contents	Features	Remarks
Op-amp.1	General-use Single power supply operational amp.	Wide output D-range: 0.2 V to $V_{CC} - 0.5$ V Low power consumption: $I_{CC} = 0.5$ mA	AN9D series
Op-amp.2	High speed Highly stable operational amp.	High speed: Cutoff frequency = 20 MHz : Slew rate = 100 V/µs	AN9D series
Op-amp.3	General-use Single power supply operational amp.	Low power consumption: $I_{CC} = 0.15 \text{ mA}$	AN9D series
Op-amp.4	General-use Single power supply operational amp.	High gain: Voltage gain = 107 dB High stability: Phase margin = 43°	AN9D series
Comp1	Low power consumption Single power supply comparator	Low power consumption: $I_{CC} = 0.1 \text{ mA}$ High speed: $t_r / t_f = 0.15 \mu\text{s}/0.3 \mu\text{s}$	AN9D series
Comp2	Single power supply High speed comparator	High speed: $t_d = 0.015 \ \mu s$	AN9D series
Reg1	General-use Stabilized power supply	High temp. stability: 150 ppm/degree or less Wide output voltage range: 1.3 V to $V_{CC} - 0.5$ V	AN9D series

Package Table

Series name		AN9DX00 series							AN9EX00 series	
Maste	r name									
Package	Pin count	AN9DA00	AN9DB00	AN9DC00	AN9DD00	AN9DE00	AN9DF00	AN9EA00	AN9EB00	AN9FA00
	16	•								
	18									
Ы	20									
DIL	22	•	•				•			
	24	•								
	28		•	•						•
	20	•					•			
	22	•					•			
	24	•	•				•			
SDIL	28		•	•		•		•	•	•
	30		•	•						•
	42		•	•						•
	52			•		•			•	•
	18									
	20	•	•				•			
	22									
SO	24	•					•			
	28	•	•	•		•	•	•	•	•
	36	•	•				•			•
	32							•		•
QPF	44								•	
	48						•		•	•
	64			•	•	•	•		•	•
	80								•	•
OFN	24	•								
QFN	44	•	•	•			•	•	•	•